

RD50-MPW2 jitter measurements

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RD50-MPW2

Resistivity 1900 Ωcm

Non-irradiated

Active pixel matrix

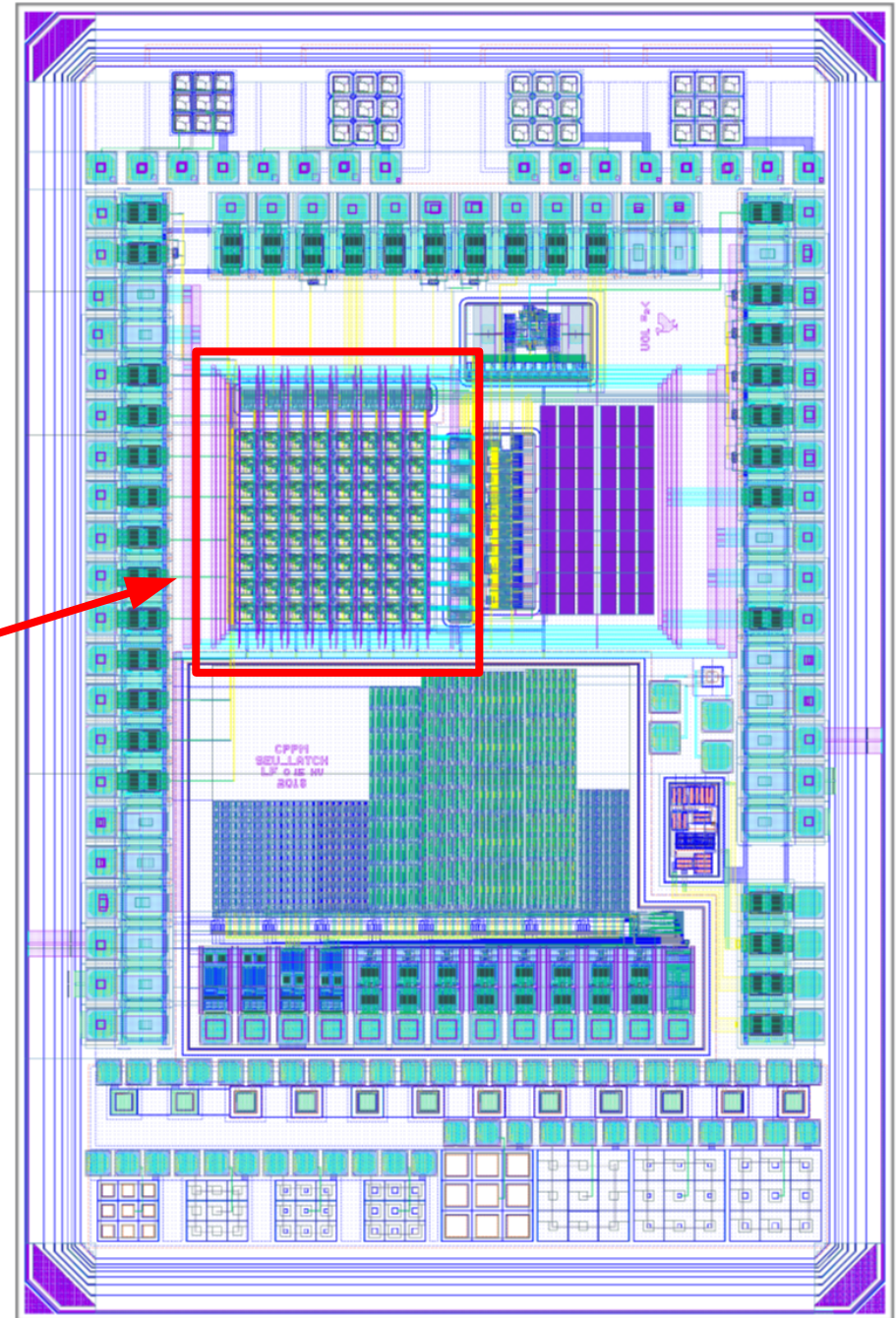
Continuous-reset pixel

Baseline = 900 mV

Threshold = 950 mV or 1000 mV

$V_{\text{bias}} = -100\text{ V}$

Time over threshold proportional to injected charge

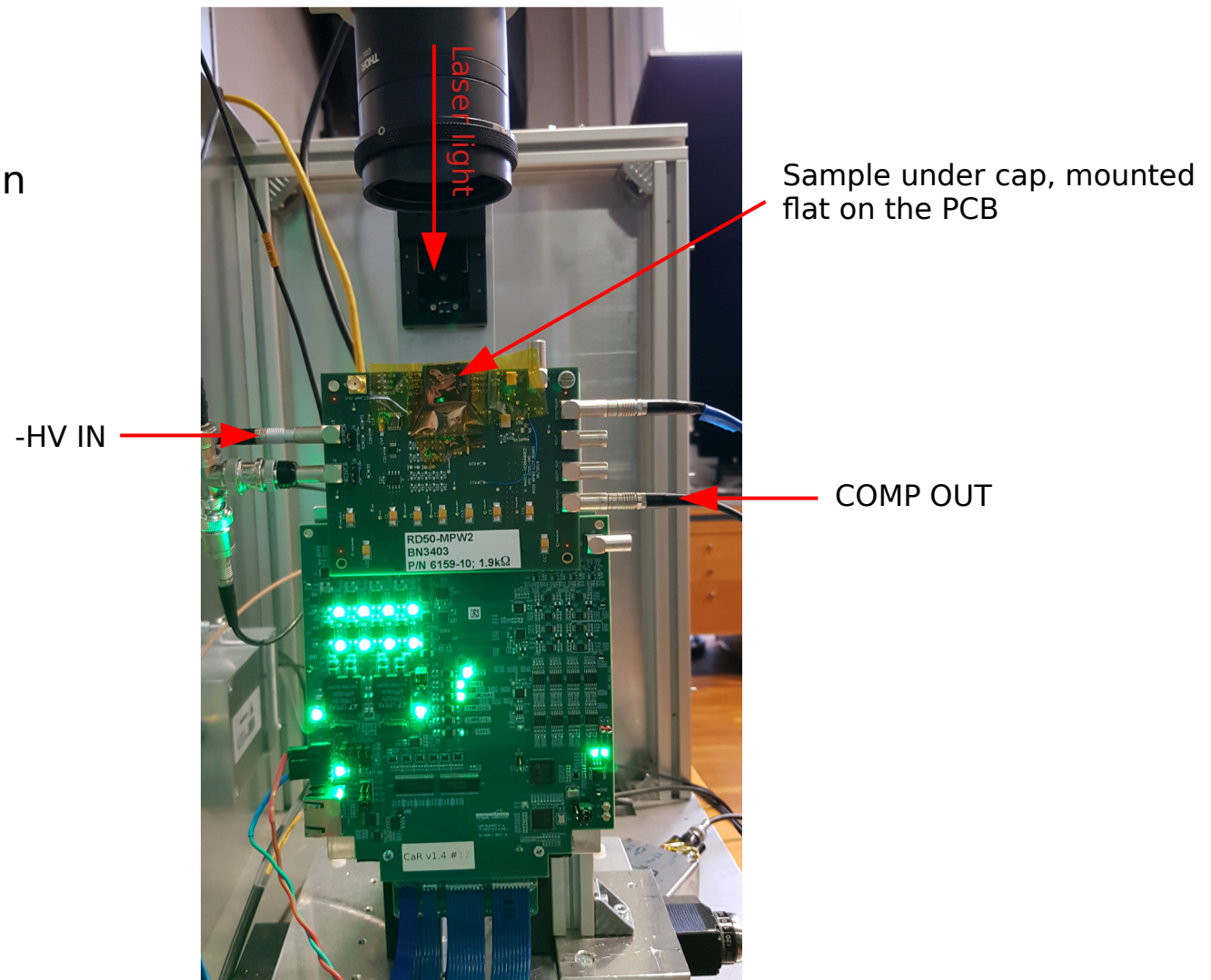


Setup

Goal: Determine the jitter of the comparator output rising edge and its positional dependence within the depleted region.

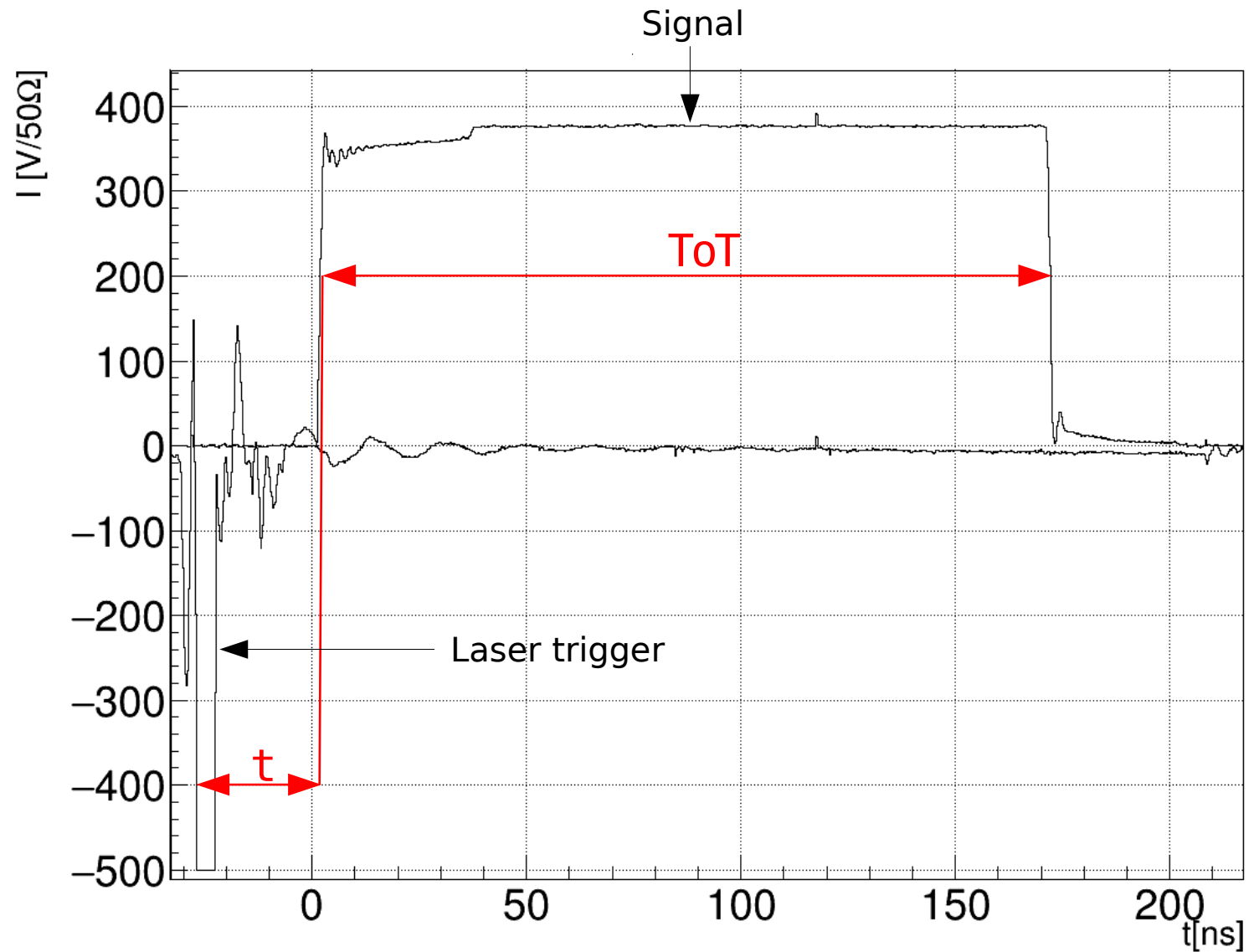
Edge-TCT configuration

1060 nm (IR) light



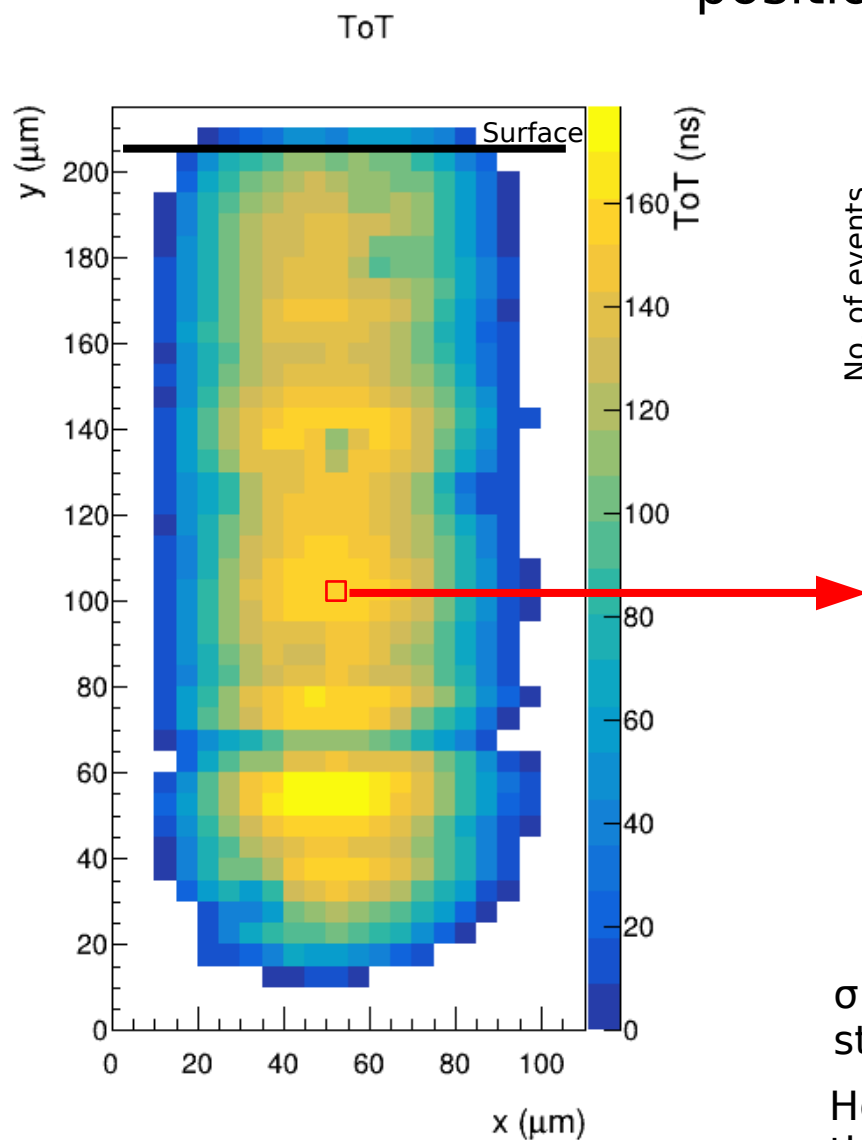
Measurements

Thresholds:
200 mV signal
-400 mV laser

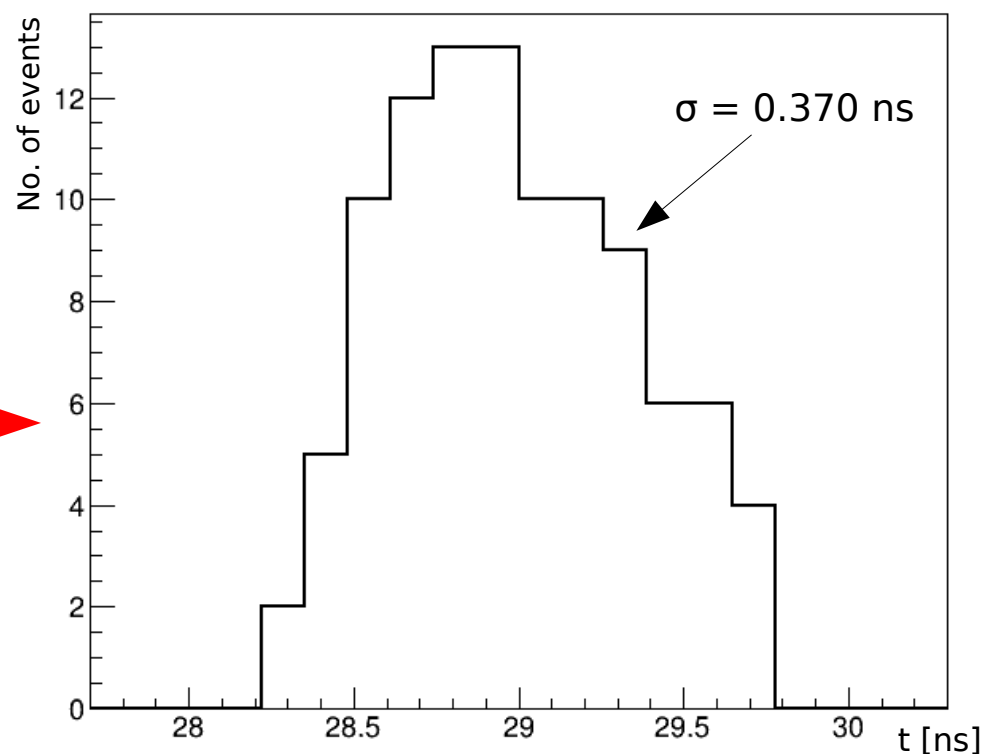


Measurements

100 waveform samples at each position



Time distribution of signal rising edge

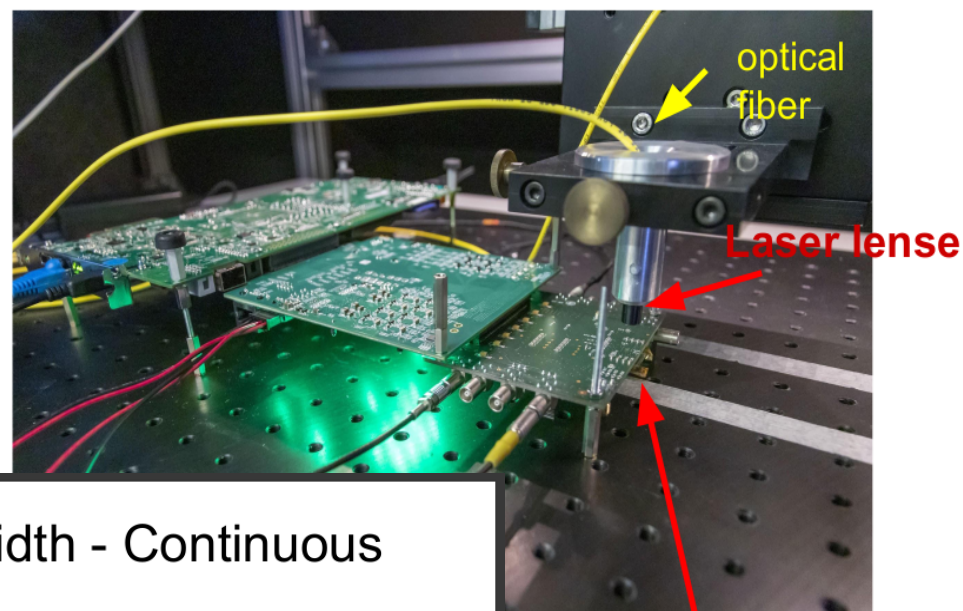


σ of spread calculated as the sample standard deviation

How does the spread depend on the signal strength?

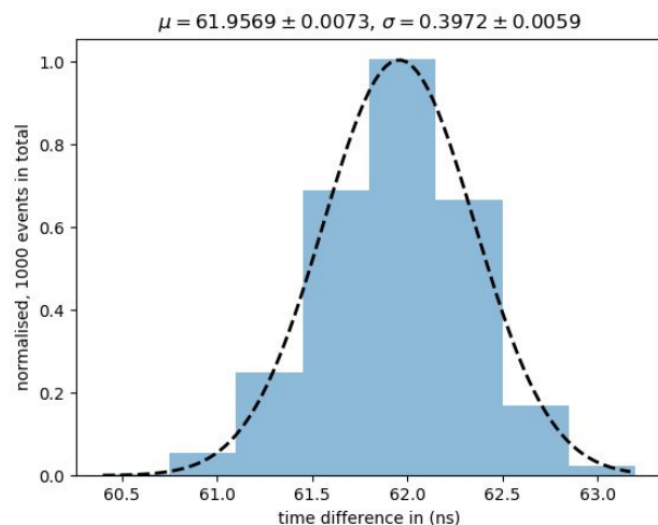
Similar measurements at the Nikhef Institute

Unfocused laser
Long laser pulses
Backside injection

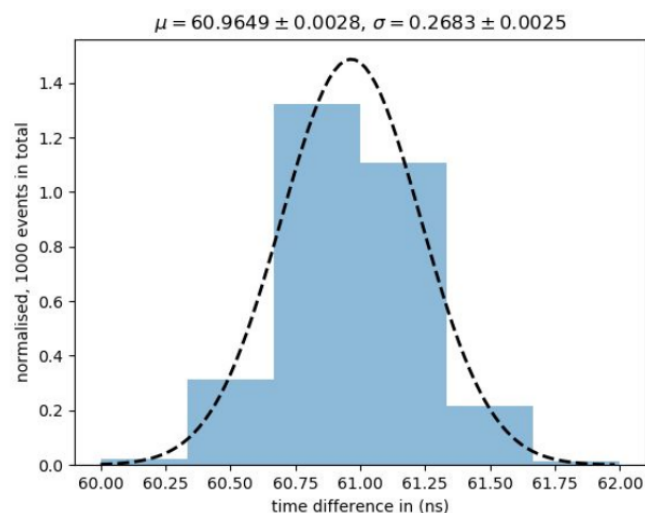


Time resolution for two different pulse width - Continuous

11ns wide injected laser pulse - Continuous pixel



17ns wide injected laser pulse - Continuous pixel



BL= 900, TH=1000, Bias Voltage = -60V

errors = errors from the fitting analysis

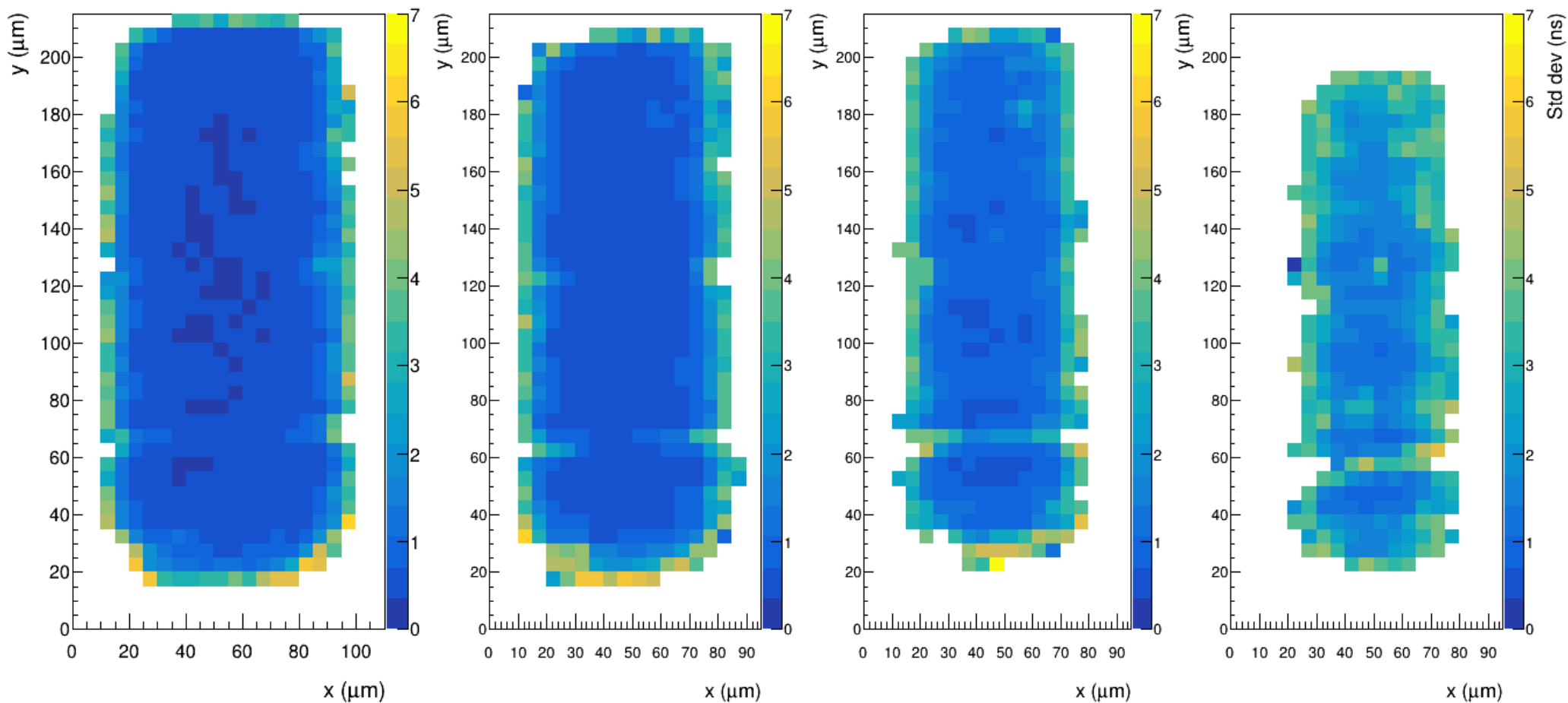
13

Results

2D scans at different laser beam intensities.

Jitter uniform throughout the center of the depleted region and increases for weaker pulses.

Sample standard deviations of 100 waveforms at each position:



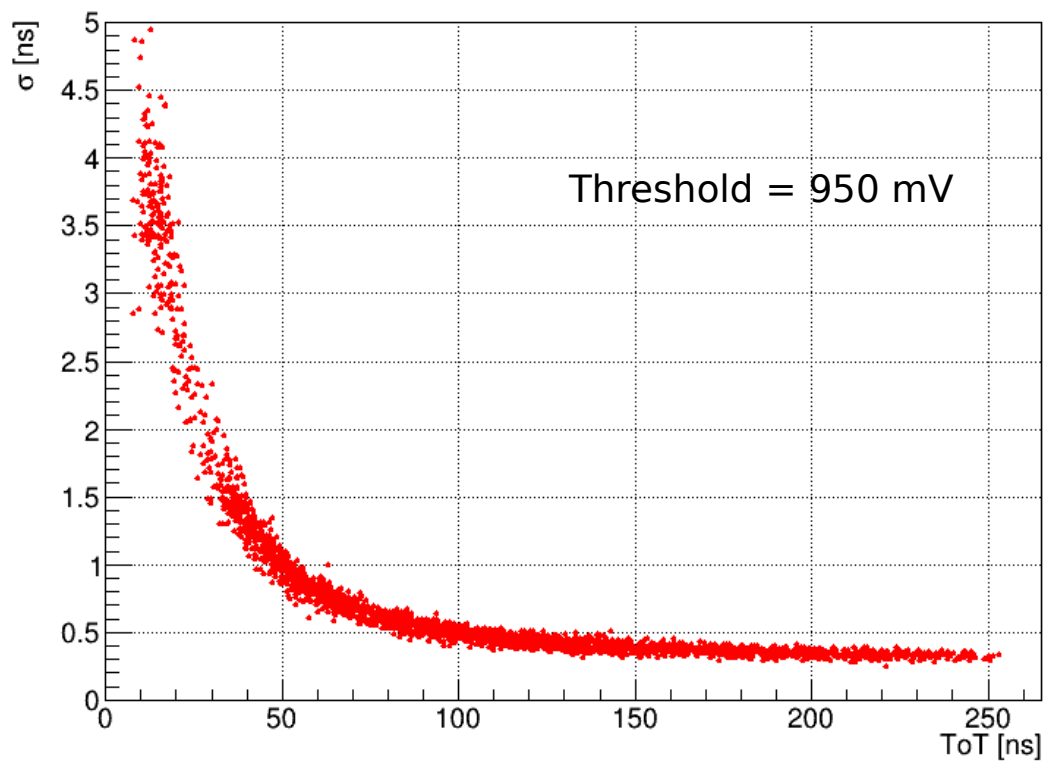
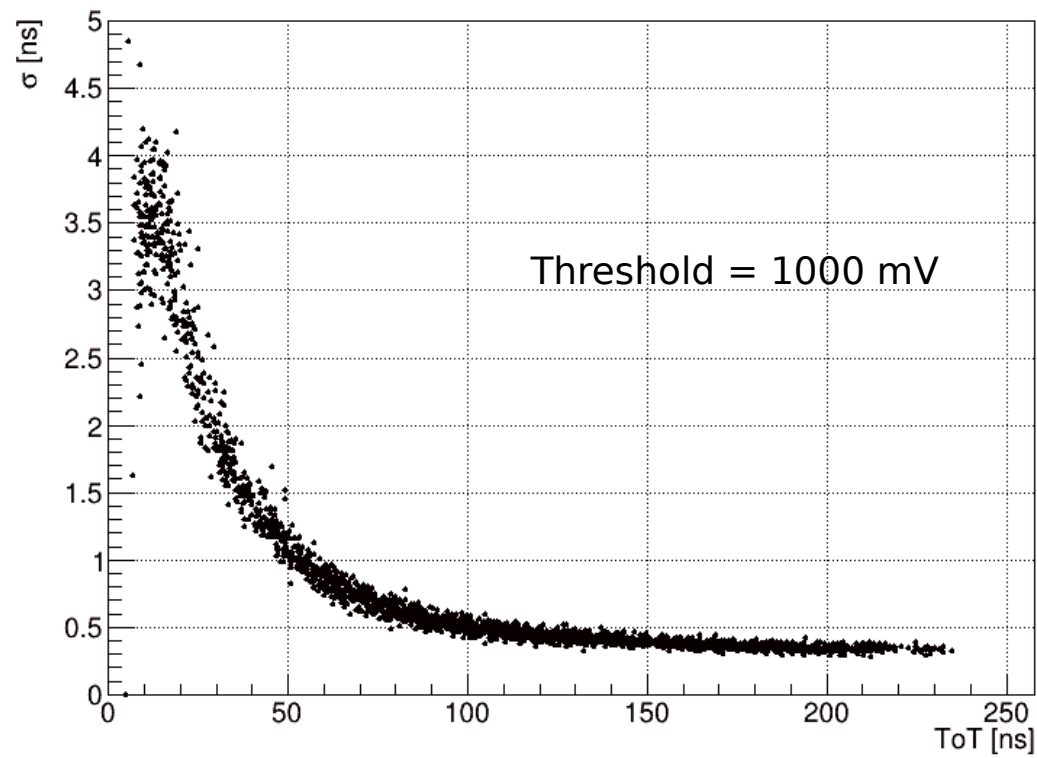
DAC 40%

DAC 50%

DAC 54%

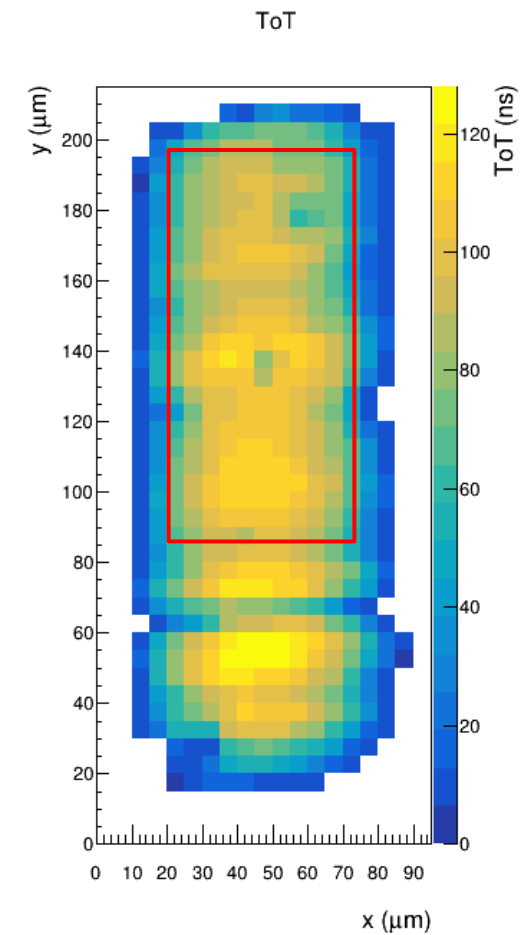
DAC 56%

Decreasing beam intensity



Points from a $110\ \mu\text{m} \times 50\ \mu\text{m}$ area at the center of the pixel

No significant differences between the two thresholds



Next steps:

Measure ToT calibration: ToT dependence on injected charge

→ We can plot σ vs amount of created charge

Measure jitter via direct charge injection to estimate laser contribution

Measure an irradiated sample ($5 \cdot 10^{14} n_{eq}/\text{cm}^2$)